

NTE159 Silicon PNP Transistor Audio Amplifier, Switch (Compl to NTE123AP)

Absolute Maximum Ratings:

Collector-Emitter Voltage, V _{CEO}	80V
Collector-Base Voltage, V _{CBO}	
Emitter-Base Voltage, V _{EBO}	5V
Continuous Collector Current, I _C	800mA
Total Device Dissipation (T _A = 25°C), P _D	
Derate Above 25°C	5mW/°C
Operating Junction Temperature Range, T _J	55° to +150°C
Storage Temperature Range, T _{stq}	55° to +150°C
Thermal Resistance, Junction to Case, R _{θJC}	83.3°C/W
Thermal Resistance, Junction to Ambient, $R_{\theta JA}$	200°C/W

Note 1. Matched complementary pairs are available upon request (NTE159MCP). Matched complementary pairs have their gain specification (h_{FE}) matched to within 10% of each other.

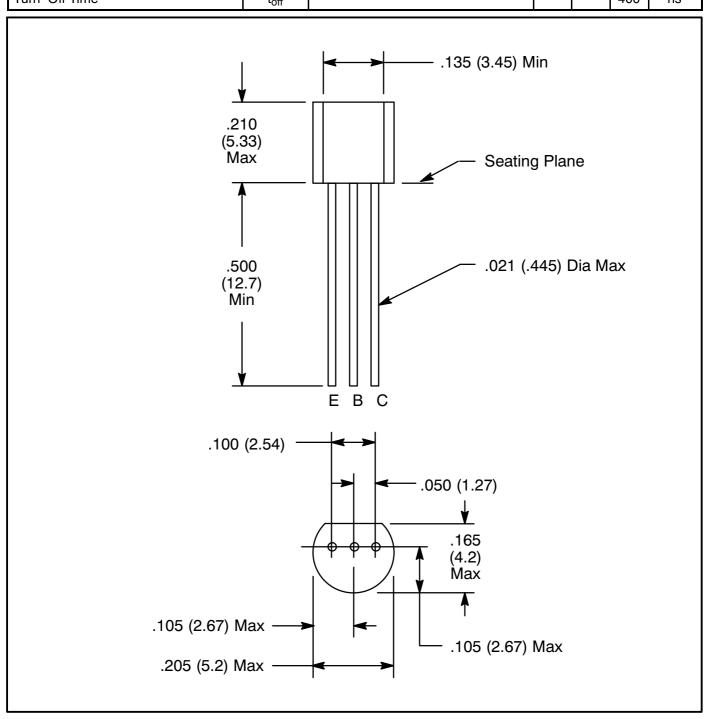
Electrical Characteristics: $(T_A = +25^{\circ}C \text{ unless otherwise specified})$

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit				
OFF Characteristics										
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C = 10mA, I _B = 0, Note 2	80	-	-	V				
Collector-Base Breakdown Voltage	V _{(BR)CBO}	$I_C = 10\mu A, I_E = 0$	80	_	-	V				
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	5	-	-	V				
Collector Cutoff Current	I _{CBO}	V _{CB} = 50V, I _E = 0	-	_	50	nA				
		$V_{CB} = 50V, I_E = 0, T_A = +75^{\circ}C$	-	_	5	μΑ				
Emitter Cutoff Current	I _{EBO}		-	_	100	nA				
ON Characteristics (Note 2)										
DC Current Gain	h _{FE}	V _{CE} = 10V, I _C = 100μA	25	-	-					
		V _{CE} = 10V, I _C = 1mA	40	-	-					
		V _{CE} = 10V, I _C = 10mA	50	-	250					
		V _{CE} = 10V, I _C = 100mA	40	-	-					
		V _{CE} = 10V, I _C = 500mA	30	_	-					
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = 150mA, I _B = 15mA	-	-	0.15	V				
		I _C = 500mA, I _B = 50mA	-	-	0.5	V				
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C = 150mA, I _B = 15mA	-	_	0.9	V				
		$I_C = 500 \text{mA}, I_B = 50 \text{mA}$	-	_	1.1	V				

Note 2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

<u>Electrical Characteristics (Cont'd)</u>: $(T_A = +25^{\circ}C \text{ unless otherwise specified})$

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit			
Dynamic Characteristics									
Output Capacitance	C _{ob}	V _{CB} = 20V, I _E = 0, f = 1MHz	-	-	30	pF			
Input Capacitance	Ci _b	V _{BE} = 500mV, f = 1MHz	-	-	110	pF			
Small-Signal Current Gain	h _{fe}	$I_C = 500$ mA, $V_{CE} = 10$ V, $f = 100$ MHz	1	-	5				
Noise Figure	NF	I_C = 100mA, V_{CE} = 10V, R_S = 1k Ω , f = 1kHz, B_W = 1Hz	_	_	3	dB			
Switching Characteristics									
Turn-On Time	t _{on}	$V_{CC} = 30V, I_C = 500mA,$ $I_{B1} = I_{B2} = 50mA$	_	_	100	ns			
Turn-Off Time	t _{off}	I _{B1} = I _{B2} = 5UMA	_	_	400	ns			



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